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				Filing Date	
				First Named Inventor	Thomas M. Crawford
				Group Art Unit	
				Examiner Name	
Sheet	1	of	1	Attorney Docket Number	SEAG 63445

FOREIGN PATENT DOCUMENTS							
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GJ		D. H. AUSTON, "Picosecond Optoelectronic Switching and Gating in Silicon," <i>Applied Physics Letters</i> , Vol. 26, No. 3, February 1, 1975, pp. 101-103.	
		J. A. VALDMANIS ET AL., "Picosecond Electro-Optic Sampling System," <i>Applied Physics Letters</i> , Vol. 41, No. 3, August 1, 1982, pp. 211-212.	
		G. BURNS, <i>Solid State Physics</i> , Academic Press, San Diego, 1985, pp. 288-289.	
		F. E. DOANY ET AL., "Carrier Lifetime Versus Ion-Implantation Dose in Silicon on Sapphire," <i>Applied Physics Letters</i> , Vol. 50, No. 8, February 23, 1987, pp. 460-462.	
		M. E. DUNHAM ET AL., "Saturation Behavior of Silicon Auston Switches," <i>Journal of Applied Physics</i> , Vol. 66, No. 1, July 1, 1989, pp. 413-418.	
		D. R. DYKAAR ET AL., "Ultrafast Coplanar Air-Transmission Lines," <i>Applied Physics Letters</i> , Vol. 57, No. 11, September 10, 1990, pp. 1123-1125.	
		Y. CHEN ET AL., "375-GHz-Bandwidth Photoconductive Detector," <i>Applied Physics Letters</i> , Vol. 59, No. 16, October 14, 1991, pp. 1984-1986.	
		U. D. KEIL ET AL., "Generation of Ultrashort Electrical Pulses With Variable Pulse Widths," <i>Applied Physics Letters</i> , Vol. 66, No. 13, March 27, 1995, pp. 1629-1631.	
✓		R. G. DECORBY ET AL., "Large (50 μm) ² Metal-Semiconductor-Metal Photodetectors With 18 GHz Bandwidth at 3 V Bias; Reduction of Hole Pileup," <i>Applied Physics Letters</i> , Vol. 73, No. 2, July 13, 1998, pp. 196-198.	
GJ		M. STELLMACHER ET AL., "Photoconductivity Investigation of the Electron Dynamics in GaAs Grown at Low Temperature," <i>Applied Physics Letters</i> , Vol. 74, No. 9, March 1, 1999, pp. 1239-1241.	

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